# ARCADIA

#### FDMAPS development with LFoundry 110nm CIS



Istituto Nazionale di Fisica Nucleare

#### <u>Manuel Rolo (INFN),</u>

#### on behalf of the **ARCADIA Collaboration.**



The second joint FCC-France&Italy Workshop on Higgs, Top, EW, HF and SM physics Venice, 4-6<sup>th</sup> November 2024

#### **ARCADIA DMAPS R&D at INFN**

Advanced Readout CMOS Architectures with Depleted Integrated sensor Arrays



- **ARCADIA:** CMOS sensor design and fabrication platform on LF11is technology
  - Sensor R&D and Technology, CMOS IP Design and Chip Integration, Data Acquisition
  - MD3: demonstrator full-chip FDMAPS for Medical (pCT), Future Leptonic Colliders and Space Instruments
  - Scalable FDMAPS architecture with very low-power: **10 mW/cm**<sup>2</sup>
  - Fully-depleted monolithic active micro strips with fully-functional embedded readout electronics
  - Ongoing R&D for the implementation of monolithic CMOS sensors with gain layer for fast timing
  - $\blacktriangleright$  Custom BSI process allow to develop fully-depleted thick sensors (400  $\mu m$ ) for X-ray imaging



#### Sensor Concepts and post-processing





- n-type high resistivity active region + n-epi layer (reduces punch-through current between p+ and deep pwells)
- sensing electrodes can be biased at low voltage (< 1V)</li>
- BSI Reverse-biased junction: depletion grows from back to top •
- Ongoing R&D: Fully Depleted PAD sensors with gain layer

HR wafers - no backside lithio





thinning, lithography, backside p+ implantation and

laser annealing, insulator and metal deposition to

create backside guardring structures

HR wafers - backside litho



implantation and laser annealing, no patterning on backside

		n-epi2
Active thickness: 48um		High Resistivity n-epi 1
	-	
		p+ substrate
		Total thickness: 300um

p+ wafers - double epi

thinning down to 100µm total thickness on a p+ starting substrate, active thickness below 50µm

4)),

### **ARCADIA Technology demonstrators**





- ARCAD
- ARCADIA-MD3 Main Demonstrator (512 x 512 pixels)
- MAPS and test structures for PSI (CH)
- MATISSE Low Power (ULP front-end for space instruments)
- $\blacktriangleright$  pixel and strip test structures down to 10  $\mu m$  pitch
- ASTRA 64-channel mixed signal ASIC for Si-Strip readout
- 32-channel monolithic strip and fully-functional readout electronics
- (ER2) HERMES: small-scale demonstrator for fast timing
- ▶ (ER3) Small-scale demonstrator of a X-ray multi-photon counter
- (ER3) Wafer splits with timing layer, new R&D towards <<50 ps timing performance: test structures and
- ▶ (ER3) MADPIX: multi-pixel active demonstrator chip for fast timing

## **ARCADIA-MD3: Chip Architecture**





- Pixel size 25 µm x 25 µm, Matrix core 512 x 512, 1.28 x 1.28 cm<sup>2</sup> silicon active area, "side-abuttable"
- Triggerless data-driven readout and low-power asynchronous architecture with clockless pixel matrix
- Event rate up to 100 MHz/cm<sup>2</sup> (design post-layout simulations)
- ▶ High-rate operation (16 Tx): 17-30 mW/cm<sup>2</sup> depending on transceiver driving strength (measured)
- Low-power operation (1 Tx): 10 mW/cm<sup>2</sup> (all data conveyed in 1 transceiver, others turned-off)

## **ARCADIA-MD3: charged particles**



**Cosmic rays** (tilted sensor)











<sup>90</sup>Sr







150 175

200 225

125

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75 100

## **ARCADIA-MD3: X-ray tube and CT**



- X-ray setup (2 mA, 40 kV) with W tube (8.40 keV and 9.67 keV) ٠
- Radiography samples and CT reconstruction (stepper motor, 1.8 deg) •



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## **ARCADIA-MD3: X-ray radioactive source**





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## Test beam with ARCADIA-MD3



- Test beam at FNAL (120 GeV protons): very good results from <u>data analysis ongoing</u>
- mini-telescope with 3 ARCADIA-MD3 200  $\mu m$  thick sensors
- Threshold, sensor HV and incidence angle parametrisation: study of cluster size, collection efficiency, spatial resolution







#### The INFN-PD Test-beam Team:

Sabrina Ciarlantini, Caterina Pantouvakis, Michele Rignanese, Alessandra Zingaretti, Piero Giubilato, Jeffery Wyss, Serena Mattiazzo, Chiara Bonini, Davide Chiappara, Devis Pantano, Patrizia Azzi e Rosario Turrisi

#### At FNAL:

Irene Zoi, Nicola Bacchetta, Artur Apresyan, Aram Hayrapetyan, Pierce Affleck

## MD3 TB Data Analysis: Cluster size



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25



- Cluster dimensions on the DUT as a function of the discriminator threshold and incidence angle
- Clusters are hits close in time and in adjacent pixels
- \* (Top) Cluster analysis is pre-tracking
- \* (Right) Multiplicity histograms linear and log scale from data sets used for tracking





## **MD3 TB Data Analysis: Spatial Resolution**





100

x [pixel]

CHIP 2

100 200 v [pixel]

500 300 400

clusters with multiplicity above 20

X [mm]

CHIP 2

12

6 <sup>8 10 12</sup>

y [mm]

4

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## **MD3 TB Data Analysis: Efficiency**





- Efficiency plot vs. Threshold, scanned from 800 down 300 e-
- Time Window = 5 µs, Spatial cut = 5 [pixels]

#### average efficiency 0.9941 +/- 0.0003



- d = spatial cut on DUT hits (pixel)
- d = 5  $\rightarrow$  11x11 matrix
- d = 3  $\rightarrow$  7x7 matrix

## **Pixel/Strip Test Structures**





#### \* pixels come in different flavours:

- Pseudo-Matrices of 1x1 and 2x2 mm<sup>2</sup>
- 50  $\mu m$  (5 variants)
- 25  $\mu m$  (3 variants)
- 10 µm (6 variants)



- and strips as well:
  - 25 μm pitch pixelated + 25 μm continuous
    (10+10) [2 variants]
  - 10 µm pixelated (4 groups of 12 strips connected to pads) [4 variants]

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## **CMOS FD Monolithic Active Microstrips**



- Design and Production of continuous and "pixelised" strips, range 10 100µm pitch
- Proof-of-concept: CMOS monolithic strips and embedded readout electronics (active sensor area is 12,8 × 3,2 mm<sup>2</sup>)
- Analogue (MUX-differential output buffer) and Digital readout (Wilkinson ADC + serialiser)





### **ARCADIA: R&D for fast timing**



#### **CMOS-LGAD**

PW NW PW	sensor pad gain layer	PW NW PW
DPW		DPW
n-epi		
п-ері		
High Resistivity Si		
n±		

#### Add-on *p***-gain** implant (gain target: **10 – 30**)



Add-on p-gain implant underneath the n+ collecting electrode to push the timing performances

Productions on ARCADIA-ER3 (25 wafers), ER4 (16 wafers) and ER5 (16 wafers, just delivered)

#### development of fully-depleted MAPS

PW  NW  PW  sensor pad    DPW	PW NW PW
n-epi	
High Reciptivity Si	

#### Standard 110 nm CMOS process at LFoundry

M. Mandurrino





TOF

Tracker

#### **ARCADIA CMOS LGADs - data from test structures**





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### MadPix CMOS LGAD multi-pixel prototype

- MadPix prototype with gain layer and integrated electronics
- first small-scale demonstrator 4 x 16 mm<sup>2</sup>;
- 8 matrices (64 pixel pads each) implementing different sensor and front-end flavours;
- 250 x 100 μm<sup>2</sup> pixel pads;
- 64 analogue outputs on each side, rolling shutter of single matrix readout;





Sensor pad



### MadPix CMOS LGAD Test Beam





#### ALICE3 TOF Test beam @ CERN PS - October 2024



#### The ALICE3 TOF Test-beam Team:

PW NW PW

DPW

gap

M. Bregant, S. Bufalino, Z. Buthelezi, D. Cavazza, M. Colocci, C. Ferrero, U. Follo, J. Goodhead, S. Förtsch, G. Gioachin, M. Mandurrino, B. Sabiu, G. Souza, S. Strazzi, S. Wimberg [INFN BO, INFN TO, iThemba LABS, U. São Paulo]

### MadPix CMOS LGAD Test Beam





- Gain layer implemented (5-15) with very good matching with TCAD simulation framework
- MadPix test beam just concluded, timing resolution measured < 75 ps (very preliminary results)
- 48  $\mu$ m thick active layer on a p+ substrate, timing resolution is sensor limited (FEE jitter ~ 20 ps r.m.s.)
- <u>Up next</u>: new short-loop with ARCADIA mask set and thinner n-epi active layer, start full-chip IP design for ALICE3 TOF

## **R&D** for a Si-Wrapper with AC-LGADs





- LGAD detector with continuous gain layer (RSD), charge collection through resistive n-layer and readout by induction on AC coupled pads, for a
- fully active detector, avoiding isolation implants (used to prevent early breakdown) in segmented LGADs
- Timing resolution approximatively independent from pixel pitch
- CMOS integration of the LGAD technology already demonstrated (in LF11is) with the ARCADIA masksets
- Up next for CMOS AC-LGAD: demonstrate the compatibility between the RSD readout scheme and the LF11is ARCADIA CMOS process flow, first prototypes in next silicon production runs - paper on the numerical proof-ofconcept describing the CMOS integration is in preparation.

#### **ARCADIA FD-MAPS: Status and Perspectives**



- \* ARCADIA: CMOS sensor design and fabrication platform on LF11is technology
  - Scalable FDMAPS architecture with very low-power: 10 mW/cm<sup>2</sup>
- Ongoing R&D for the implementation of monolithic CMOS sensors with gain layer for fast timing, baseline technology for the ALICE3 Time-of-Flight detector
  - Scheduled runs for IP design and optimisation of the sensor technology towards excellent timing performance
- Funding available to start new joint R&D programs towards system-grade chips for FCC
  - IP development (shunt LDOs, chip-to-chip data transmission blocks), optimisation towards system-grade I/O interface, optimisation of the front-end intrinsic timing performance

**ARCADIA** LF11is FD-MAPS technology support through **DRD7.6a** (Common Access to selected imaging technologies)



## LF11is FDMAPS development through DRD7





- Possibility to explore multiple wafer splits: n-epi thickness, n-type or p-type starting substrate, substrate resistivity, FSI or BSI process on different wafer thicknesses, use of a gain layer for the implementation of monolithic CMOS LGADs.
- INFN and LFoundry agree on the terms to allow for the participation of third-party design groups to joint LF11is production runs, enabling straightforward and low-risk ramp-up of the R&D on FDMAPS using LF11is technology for new design teams.
- Silicon-proven sensor concepts and CMOS IP available (Serialisers, c-LVDS Transceivers, bandgap/LDO, SPI, DAC/ADCs).

Further information on DRD7 workshop 25-26 September 2023: <u>https://indico.cern.ch/event/1318635/</u>







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Thank you for your time!



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## **ARCADIA-MD3 TB Data Analysis**



- <u>Tracking</u> done with events with just one cluster per plane
- <u>Alignment</u>: one external plane as reference + one cluster per plane to calculate residuals
  - Other external plane aligned using correlation plots
  - Central plane DUT aligned with residuals
  - Tilt correction done using plot expected coord-x vs residual coord-y and viceversa
  - Realignment after tilt correction with residuals
  - Final Alignment to center residual in zero
- <u>Clusters</u> are hits close in time (in a certain time window) and in adjacent pixels (no "holes")
- Efficiency calculated with a fiducial region 11x11 pixel (275 um) considering hits arrived in the sensor area [0,512]
  - after alignment some row or col values are shifted outside the sensor area
  - If more than one cluster is found on DUT, consider the closest one respect to the expected hit in the efficiency calculation.



